

GaAs MMIC
Double-Balanced
4 to 8 GHz Mixer

HMC129

JANUARY 1994

Features

CONVERSION LOSS:

10 dB

LO TO RF AND IF ISOLATION:

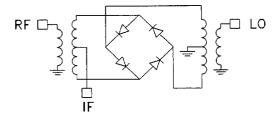
> 30 dB

SMALL SIZE, NO DC BIAS REQUIRED

General Description

The HMC129 chip is a miniature double-balanced mixer which can be used as an upconverter or downconverter in the 4 to 8 GHz band. The chip can be integrated directly into hybrid MICs without DC bias or external baluns to provide an extremely compact mixer.

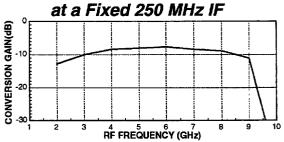
Schematic

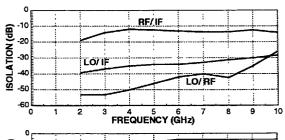


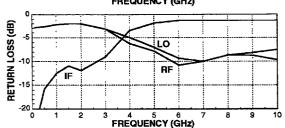
Electrical Performance (With LO Drive of +15 dBm)



Typical Performance







(With 20 Dive of 110 ability		FREGUENCT (GHZ)			
Parameter	Min.	Тур.	Max.	Units	
Frequency Range, RF & LO		4.0 - 8.0		GHz	
Frequency Range, IF		DC - 3		GHz	
Conversion Loss		8	10	dB	
Noise Figure (SSB)		8	10	dB	
LO to RF Isolation	30	40		dB	
LO to RF Isolation	20	30		dB	
IP3 (Input)	15	20		dBm	
IP2 (Input)	35	40		dBm	
1 dB Gain Compression (Input)	5	10		dBm	
Local Oscillator Drive Level	10	15	20	dBm	

21 Cabot Road, Woburn, Massachusetts 01801 Phone: 617-933-7267 FAX: 617-932-8903



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Handling Precautions

Follow these precautions to avoid permanent damage.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

Static Sensitivity: Follow ESD precautions.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip has fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

Eutectic Die Attach:

A 80/20 gold tin preform is recommended with a work surface temperature of 255 deg. C and a tool temperature of 265 deg. C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 deg. C.

DO NOT expose the chip to a temperature greater than 320 deg. C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach:

Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position.

Cure epoxy per the manufacturer's schedule.

Wire Bonding

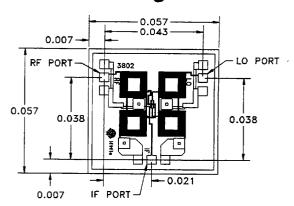
Ball or wedge bond with 1.0 diameter pure gold wire. Thermosonic wirebonding with a nominal stage temperature of 150 deg. C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds.

Wirebonds should be started on the chip and terminated on the package. RF bonds should be as short as possible.

Absolute Maximum Ratings

l .	+27 dBm
	-65 to +150 deg C
Operating Temperature	-55 to +125 deg C

Outline Drawing



DIE THICKNESS IS 0.004, BACKSIDE IS GROUND BONDPADS ARE 0.004 SQUARE ALL DIMENSIONS IN INCHES. +/-0.001

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